

L850-66-60-130 IRED illuminator with PMMA lens cap and heat sink

L850-66-60-130 is an extremely high beam and output power illuminator assembled with a total of 60 high efficiency AlGaAs diode chips, mounted on a metal stem TO-66 with AlN ceramics and sealed with glass ball lens cap and with heat sink for high current use.

◆ Features

- 1) High beam
- 2) Compact (TO-66) package
- 3) High output power

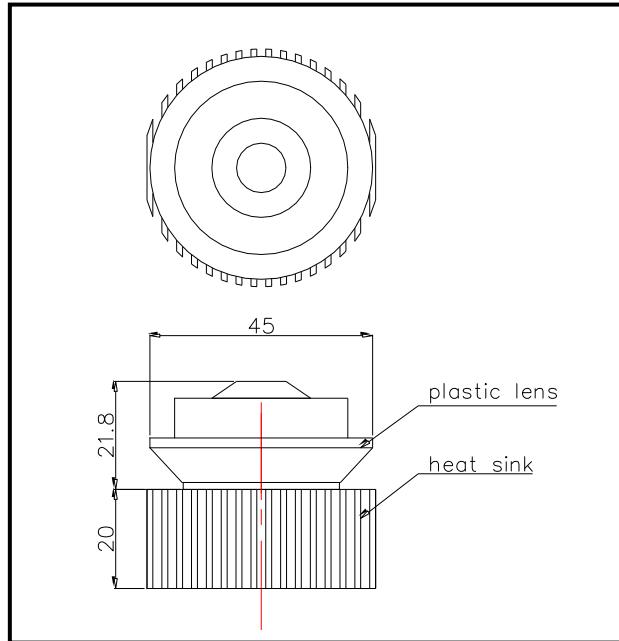
◆ Applications

- 1) For IR search light
- 2) For CCD lighting

◆ Specifications

- 1) Product name IR illuminator
- 2) Spec. No. L850-66-60-130
- 3) Chip
 - (1) Material AlGaAs
 - (2) Peak wavelength 850nm
- 4) Package
 - (1) Stem TO-66 stem with AlN
 - (2) Lens PMMA lens
 - (3) Heat sink Aluminum

◆ Outer dimension (Unit: mm)



◆ Absolute Maximum Ratings

Item	Symbol	Maximum Rated Value	Unit	Ambient Temp.
Power Dissipation	P _D	7.5	W	T _a =25°C
Forward Current	I _F	1.2	A	T _a =25°C
Pulse Forward Current	I _{FP}	6	A	T _a =25°C
Reverse Voltage	V _R	50	V	T _a =25°C
Operating Temperature	T _{OPR}	-30 ~ +80	°C	
Storage Temperature	T _{STG}	-30 ~ +110	°C	
Soldering Temperature	T _{SOL}	265	°C	

‡Pulse Forward Current condition: Duty=1% and Pulse Width=1us.

‡Soldering condition : Soldering condition must be completed within 5 seconds at 265°C

◆ Electro-Optical Characteristics (T_a=25°C)

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Total Radiated Power	P _o	I _F =800mA		950		mW
Total Radiated Power	P _o	I _{FP} =5A		5500		mW
Radiant Intensity	I _E	I _F =800mA		(6,500)		mW/sr
Axial Radiated Power	I	I _F =800mA		0.55		mW/cm ²
Forward Voltage	V _F	I _F =800mA		7.50		V
Peak Wavelength	λ _P	I _F =800mA	840	850	860	nm
Half Width	Δλ	I _F =800mA		40		nm
Viewing Half Angle	θ _{1/2}	I _F =800mA		±12		deg.
Rise Time	t _f	I _F =100mA		15		ns
Fall Time	t _r	I _F =100mA		10		ns

‡Axial Radiated Power condition: L=1m

‡LED is required to keep less than 60°C.

